

ABSTRACT

Semiconductor devices formed in fully or partially compensated semiconductor, (substrate or epi-layer), including
5 minimal current flow voltage switching devices with at least one junction which is rectifying when the semiconductor is caused to be N or P-type by the presence of applied gate voltage field induced carriers, such as inverting and non-inverting gate voltage channel induced semiconductor single devices with
10 operating characteristics similar to conventional multiple device CMOS systems.

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